

### SOT-23



### Pin Definition:

1. Gate
2. Source
3. Drain

### Key Parameter Performance

Parameter	Value	Unit
$V_{DS}$	-20	V
$R_{DS(on)}$ (max)	$V_{GS} = -4.5V$	50
	$V_{GS} = -2.5V$	65
	$V_{GS} = -1.8V$	85
$Q_g$	9.6	nC

### Features

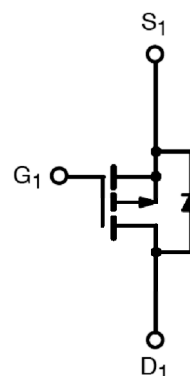
- Fast Switching
- Suited for -1.8V Gate Drive Applications
- Halogen-free

### Ordering Information

Part No.	Package	Packing
TSM500P02CX RFG	SOT-23	3Kpcs / 7+Reel

**Note:** %G+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### Block Diagram



P-Channel MOSFET

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	-4.7
		$T_C = 100^\circ C$	-3
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	-18.8	A
Power Dissipation @ $T_C = 25^\circ C$	$P_D$	1.56	W
Operating Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ C$

### Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{JA}$	80	$^\circ C/W$

### Electrical Specifications (T<sub>C</sub> = 25°C unless otherwise noted)

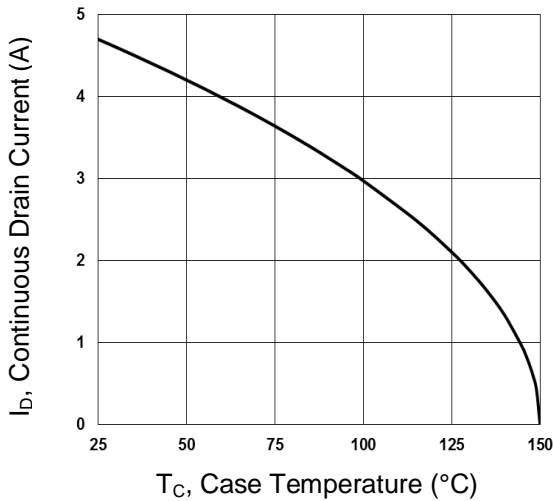
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	BV <sub>DSS</sub>	-20	--	--	V
Drain-Source On-State Resistance	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A	R <sub>DS(ON)</sub>	--	42	50	m
	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2A		--	57	65	
	V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1A		--	75	85	
Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	V <sub>GS(TH)</sub>	-0.3	-0.6	-0.8	V
Zero Gate Voltage Drain Current	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	I <sub>DSS</sub>	--	--	-1	μA
	V <sub>DS</sub> = -16V, T <sub>J</sub> = 125°C		--	--	-10	
Gate Body Leakage	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V	I <sub>GSS</sub>	--	--	±100	nA
Forward Transconductance (Note 2)	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3A	g <sub>fs</sub>	--	7	--	S
<b>Dynamic</b>						
Total Gate Charge (Note 2,3)	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3A, V <sub>GS</sub> = -4.5V	Q <sub>g</sub>	--	9.6	--	nC
Gate-Source Charge (Note 2,3)		Q <sub>gs</sub>	--	1.6	--	
Gate-Drain Charge (Note 2,3)		Q <sub>gd</sub>	--	2	--	
Input Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz	C <sub>iss</sub>	--	850	--	pF
Output Capacitance		C <sub>oss</sub>	--	70	--	
Reverse Transfer Capacitance		C <sub>rss</sub>	--	55	--	
<b>Switching</b>						
Turn-On Delay Time (Note 2,3)	V <sub>DD</sub> = -10V, I <sub>D</sub> = -1A, V <sub>GS</sub> = -4.5V, R <sub>GEN</sub> = 25	t <sub>d(on)</sub>	--	6	--	ns
Turn-On Rise Time (Note 2,3)		t <sub>r</sub>	--	21.6	--	
Turn-Off Delay Time (Note 2,3)		t <sub>d(off)</sub>	--	51	--	
Turn-Off Fall Time (Note 2,3)		t <sub>f</sub>	--	13.8	--	
<b>Source-Drain Diode Ratings and Characteristic</b>						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I <sub>S</sub>	--	--	-4.7	A
Maximum Pulse Drain-Source Diode Forward Current		I <sub>SM</sub>	--	--	-18.8	A
Diode-Source Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	V <sub>SD</sub>	--	--	-1	V

#### Note:

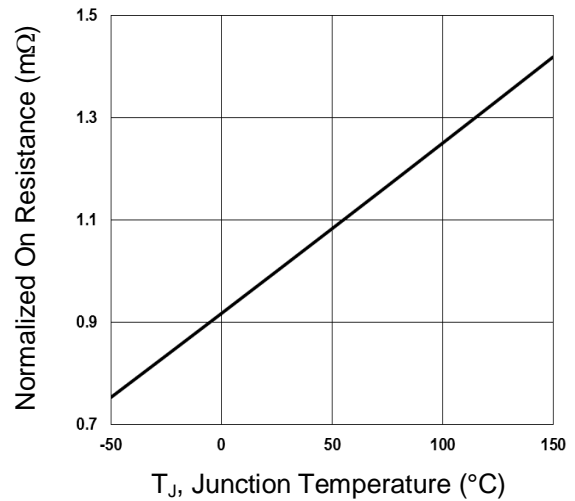
1. Pulse width limited by safe operating area
2. Pulse test: pulse width m300μs, duty cycle m2%
3. Switching time is essentially independent of operating temperature.

### Electrical Characteristics Curves

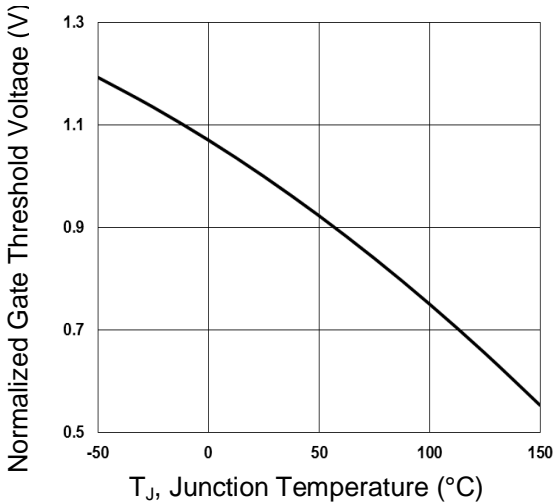
**Continuous Drain Current vs. Tc**



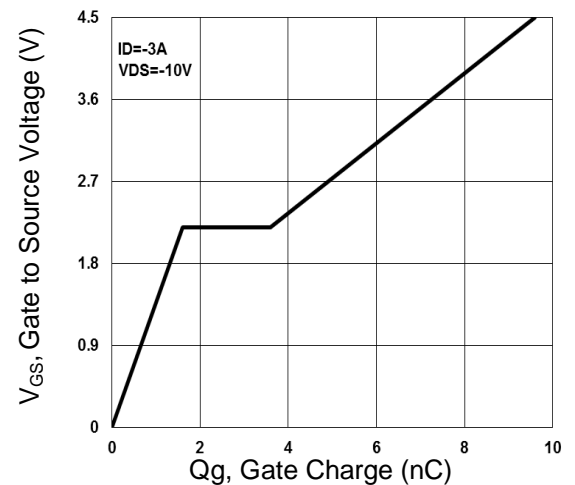
**Normalized RDSON vs. Tj**



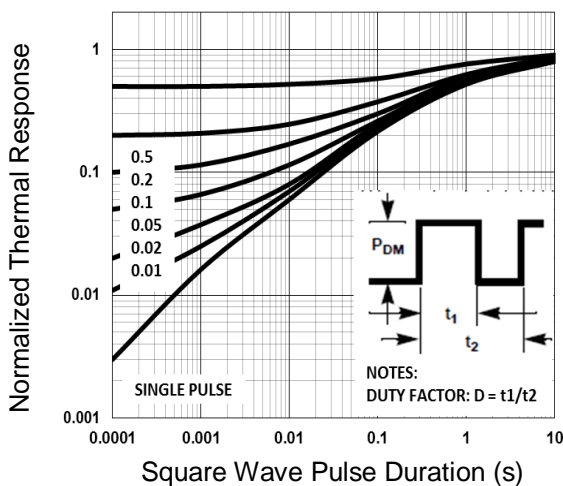
**Normalized  $V_{th}$  vs. Tj**



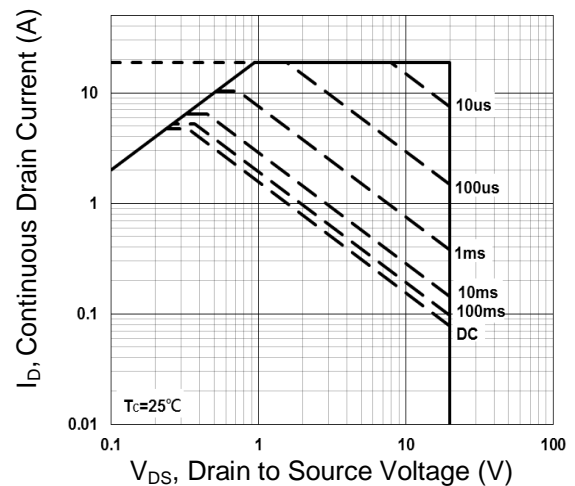
**Gate Charge Waveform**



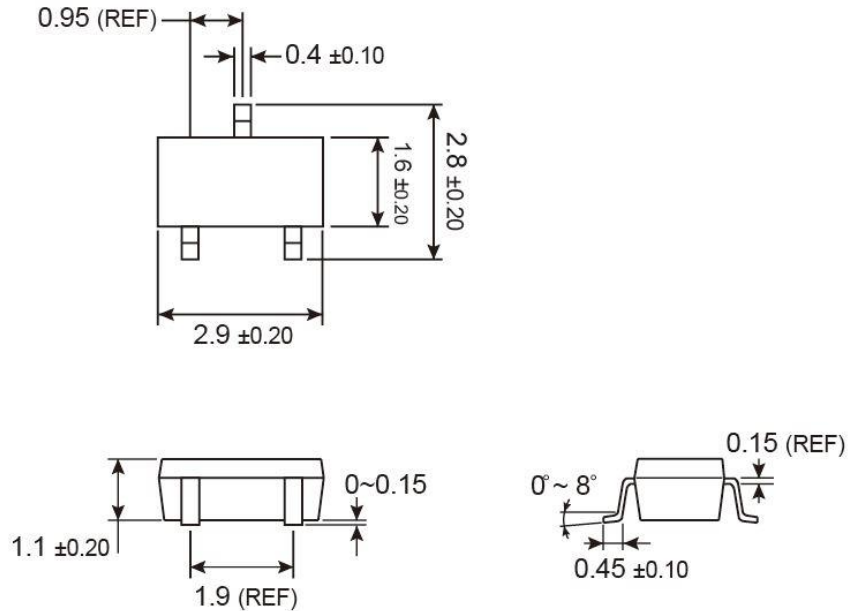
**Normalized Transient Impedance**



**Maximum Safe Operation Area**

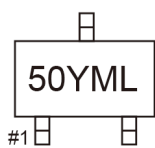


### SOT-23 Mechanical Drawing



Unit: Millimeters

### Marking Diagram



- 50** = Device Code
- Y** = Year Code
- M** = Month Code for Halogen Free Product  
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

# TSM500P02CX

## 20V P-Channel Power MOSFET

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